

Supplementary Information for

Edge-Oriented SnS₂ Nanosheet Arrays on Carbon Paper as Advanced Binder-Free Anodes for Li-Ion and Na-Ion Batteries

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Fig. S1 (a) Digital photos of commercial filter paper and its carbonized paper; (b) Demonstration of mechanical flexibility of the carbon paper.

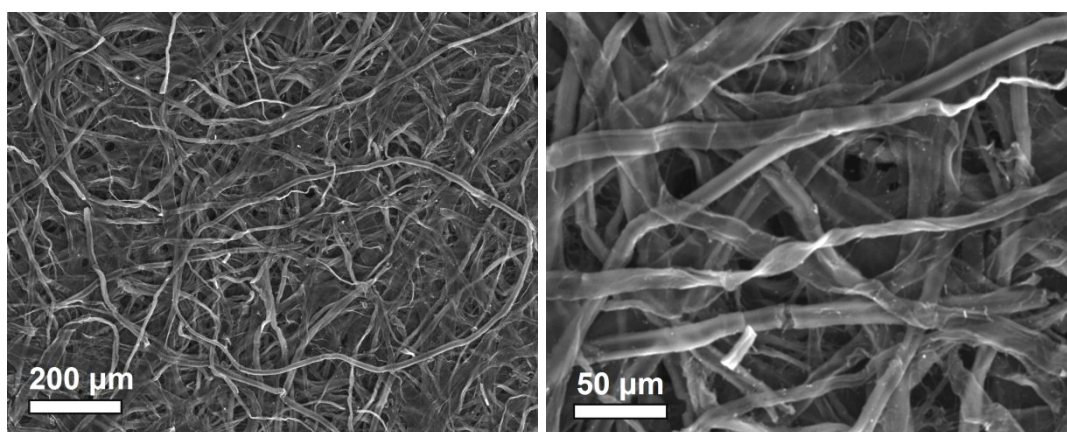


Fig. S2 SEM images of carbon microbelts derived from commercial filter paper.

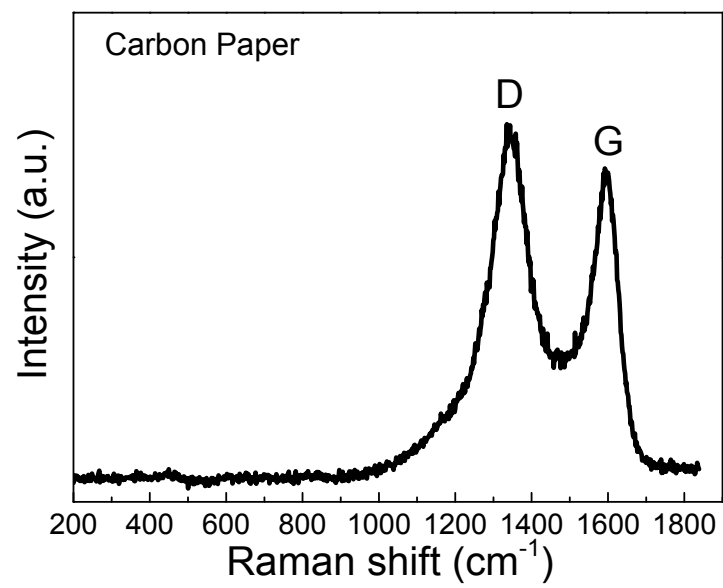


Fig. S3 Raman spectrum of the carbon paper.

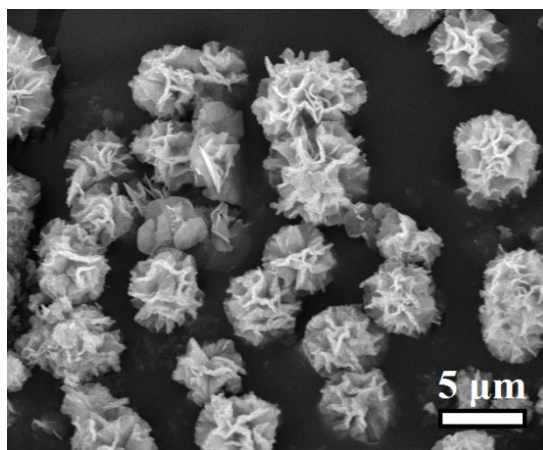


Fig. S4 SEM image of pure SnS₂ flower-like microspheres.

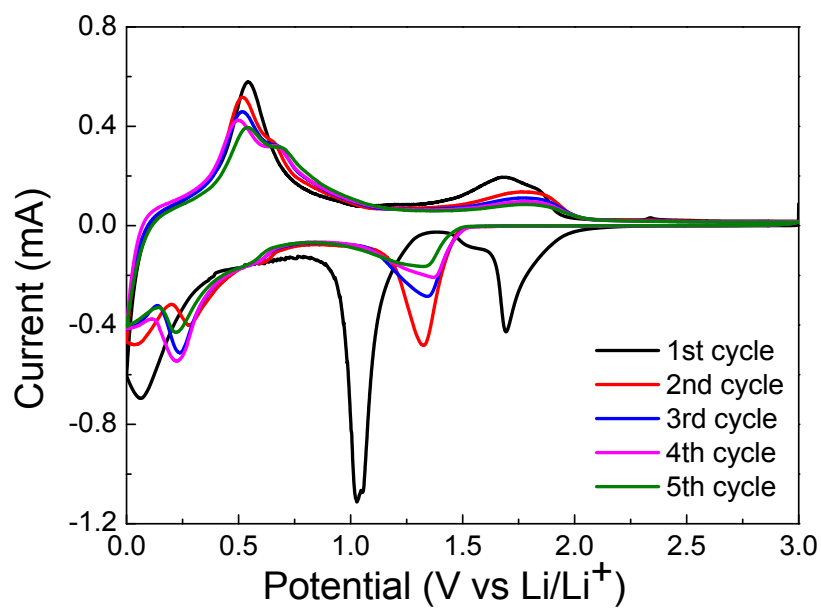


Fig. S5 CV curves of pure SnS_2 anode.

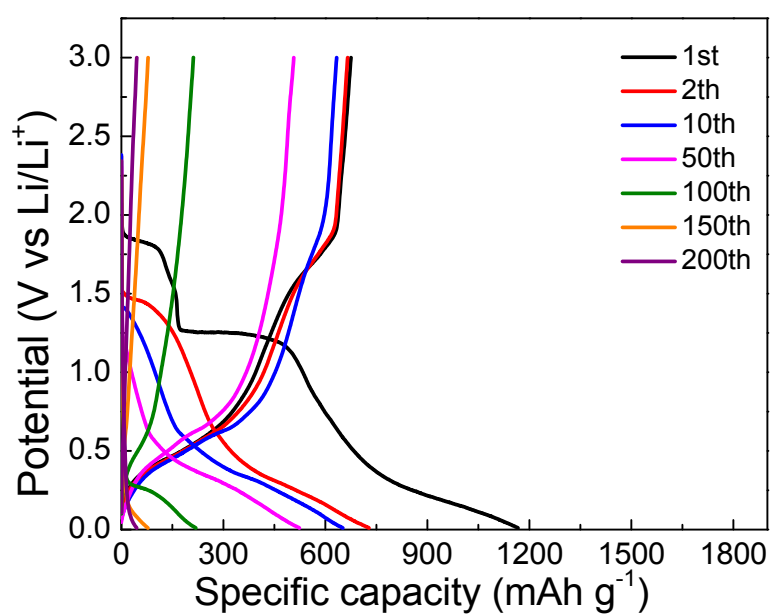


Fig. S6 Galvanostatic charge/discharge curves of pure SnS_2 anode at different cycles.

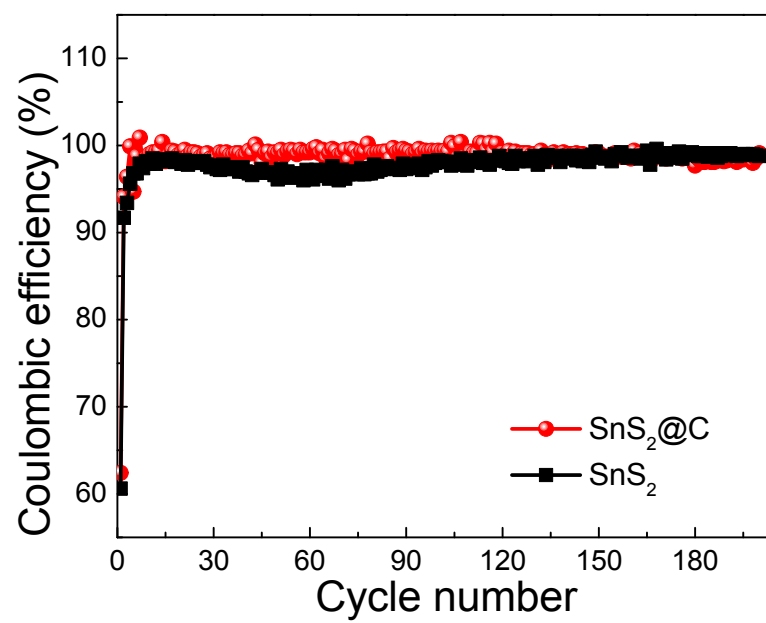


Fig. S7 Comparison of Coulombic efficiency.

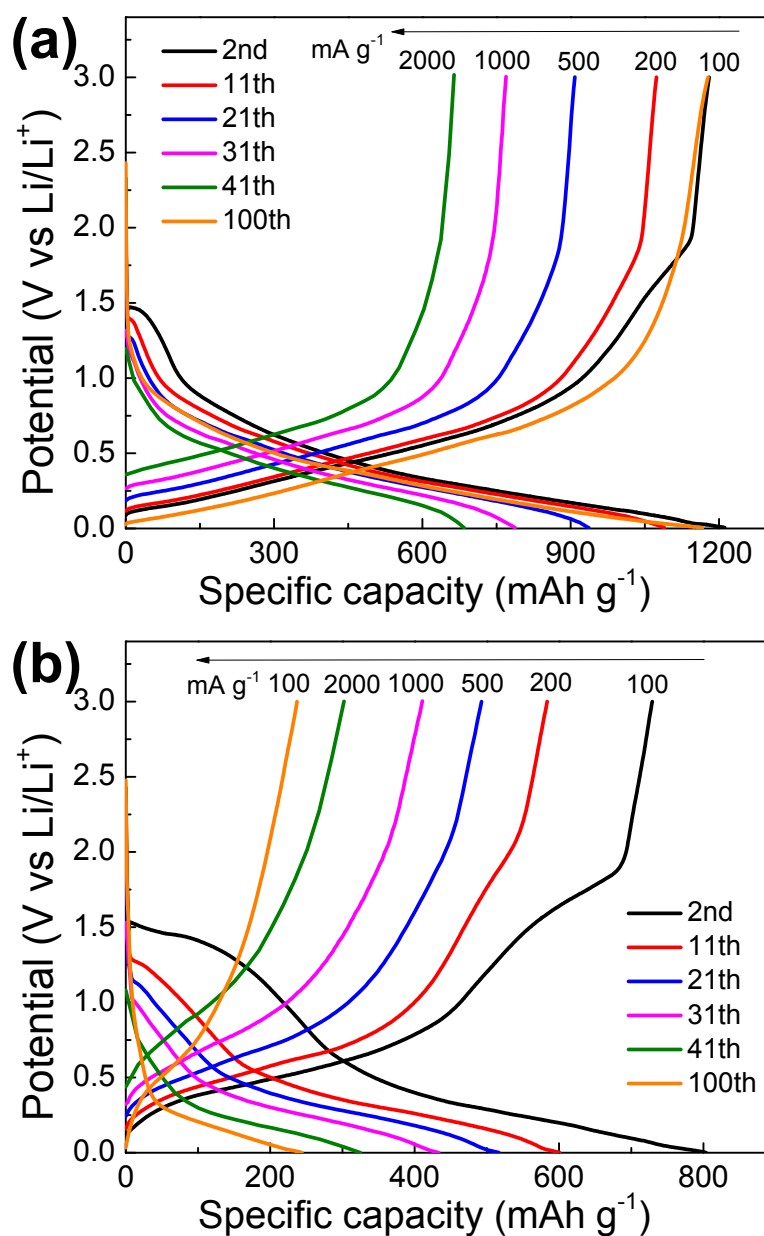


Fig. S8 Galvanostatic charge/discharge curves of (a) $\text{SnS}_2@\text{C}$ and (b) pure SnS_2 anodes at current densities from 100 to 2000 mA g^{-1} .

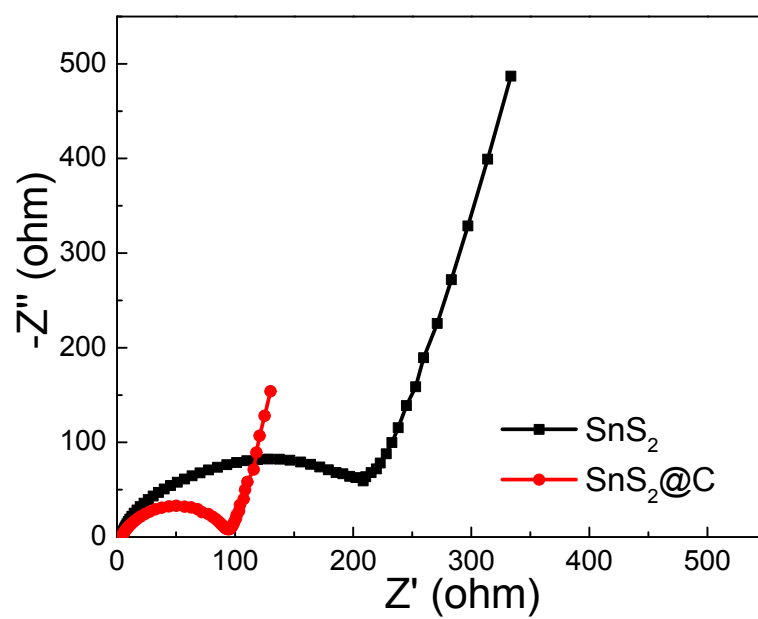


Fig. S9 Nyquist plots of the $\text{SnS}_2@\text{C}$ and pure SnS_2 anodes.

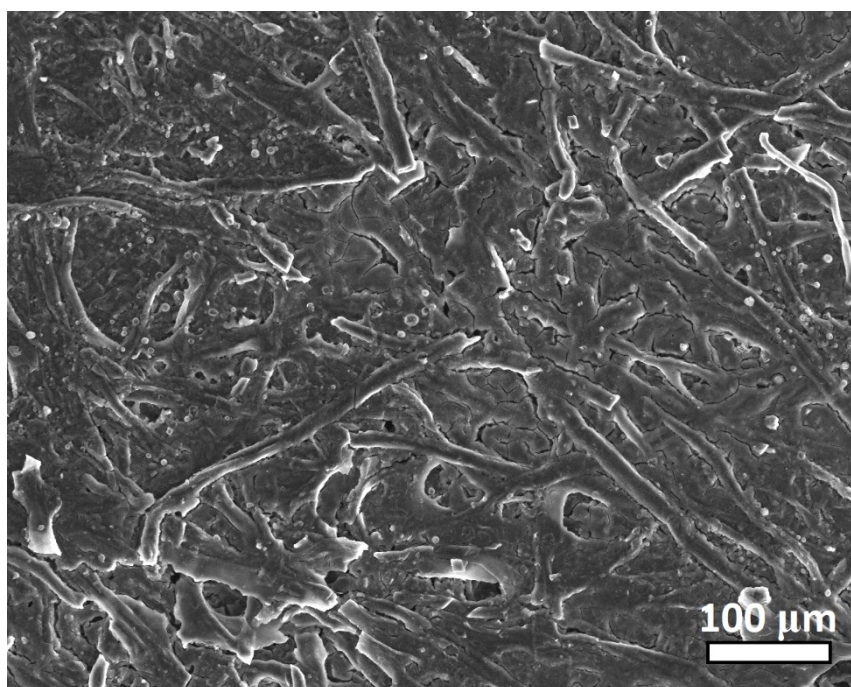


Fig. S10 SEM image of the SnS₂@C after long-term cycling test.

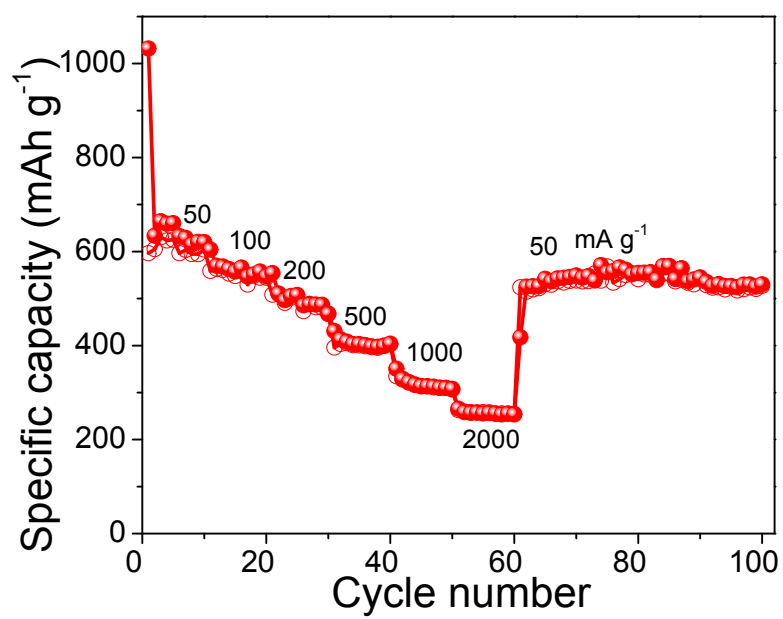


Fig. S11 Rate performance of the SnS₂@C anode for Na-ion batteries.

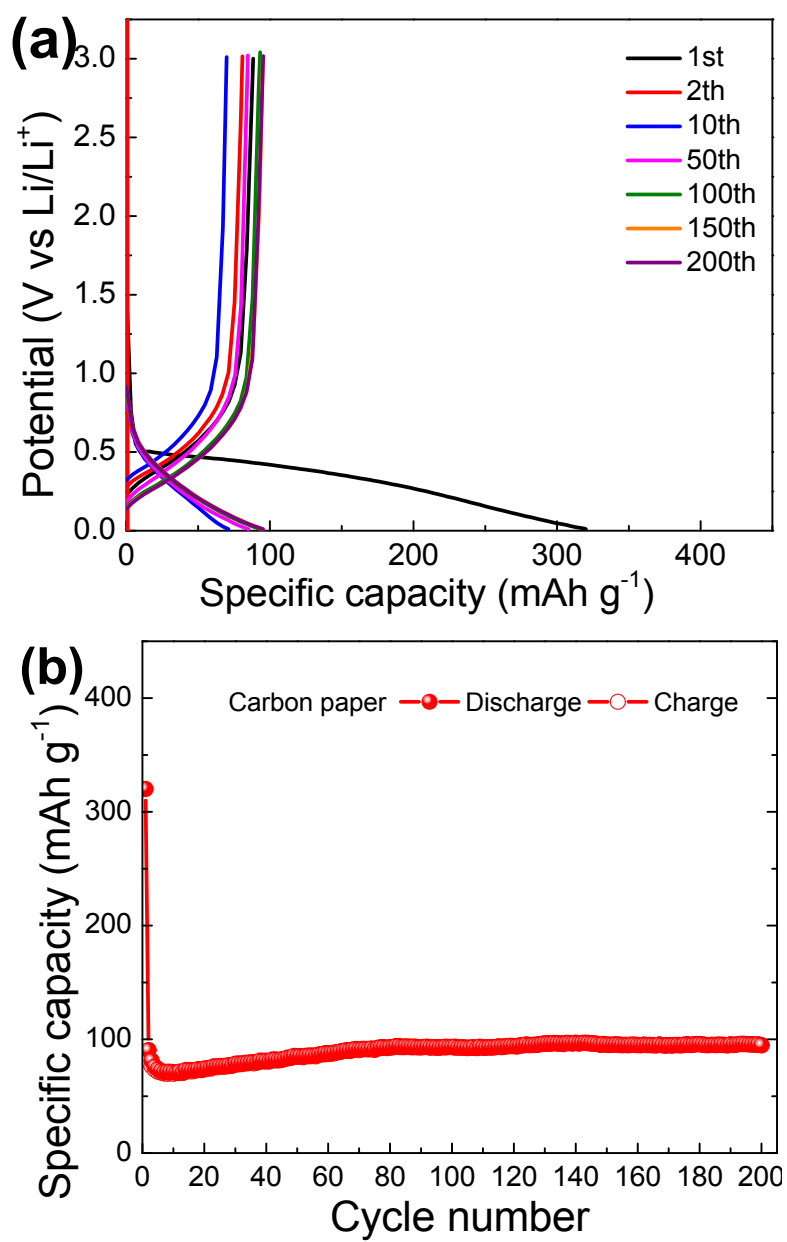


Fig. S12 (a) Galvanostatic charge/discharge curves of the carbon paper at 100 mA g⁻¹ and (b) specific capacity as a function of cycle number.

Table S1 Comparison of the reversible capacity, cycling stability and initial Coulombic efficiency (CE) of various SnS₂-based materials in Li-ion batteries.

Material ^[1]	SnS ₂ Morphology	1 st reversible capacity (mAh g ⁻¹)	Current density (mA g ⁻¹)	Capacity retention (cycle number)	1 st Coulombic efficiency	Ref.
SnS ₂	Microsphere	771	650	74% (100)	28%	[1]
SnS ₂	Nanosheet	535	100	96% (50)	-	[2]
SnS ₂	Nanoplate	1028	200	91% (30)	72.6%	[3]
SnS ₂	Nanoplate	579	100	90% (50)	40.3%	[4]
SnS ₂	Nanoflower	537	100	69% (50)	30.6%	[5]
SnS ₂	Microflower	642	200	65% (100)	36%	[6]
SnS ₂	Nanoplate	645	323	85% (30)	49.2%	[7]
SnS ₂ /graphene	Nanoplate	864	50	704 (100)	69%	[8]
SnS ₂ /graphene	Nanoparticle	738	120	76.5% (60)	71.5%	[9]
SnS ₂ /graphene	Nanocrystal	1278	65	80.9% (200)	78.8%	[10]
SnS ₂ /graphene	Nanoplate	687	50	94.6% (30)	36.2%	[11]
SnS ₂ /graphene	Nanoparticle	1002	65	57.6% (50)	-	[12]
SnS ₂ /graphene	Nanoplate	1485	50	44.2% (30)	37%	[13]
SnS ₂ /graphene	Nanoparticle	542	325	93% (200)	34.5%	[14]
SnS ₂ /graphene	Nanosheet	705	100	130.5% (50)	42.4%	[15]
SnS ₂ /graphene	Nanoparticle	569	200	98.8% (200)	34%	[16]
SnS ₂ /graphene	Nanoflake	1216	80	61.1% (100)	66%	
SnS ₂ /graphene/CNT	Nanosheet	1118.2	100	91% (100)	63%	[17]
SnS ₂ /CNT	Nanosheet	557	100	75.4% (50)	37.2%	[18]
SnS ₂ /AB	Nanoflower	622.8	400	73.1% (100)	53.5%	[19]
SnS ₂ /C	Nanosheet	665.8	100	64.4% (50)	42.9%	[20]
SnS ₂ /C	Nanoparticle	707	50	94.5% (50)	41%	[21]
SnS ₂ /PANI	Nanoplate	968.7	100	75.4% (80)	69.4%	[22]
SnS₂@C	Nanosheet	1156	100	99.5% (200)	62.5%	This work

[1] CNT: carbon nanotube; AB: acetylene black; PANI: polyaniline;

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